# **3-Input NOR Gate**

# **NL17SZ27**

The NL17SZ27 is a high performance 3-input NOR gate operating from a 1.65 V to 5.5 V supply.

#### **Features**

- Designed for 1.65 V to 5.5 V V<sub>CC</sub> Operation
- 2.6 ns  $t_{PD}$  at  $V_{CC} = 5 \text{ V (Typ)}$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I<sub>OFF</sub> Supports Partial Power Down Protection
- Source/Sink 32 mA at 4.5 V
- Available in SC-88, SC-74, and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

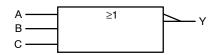
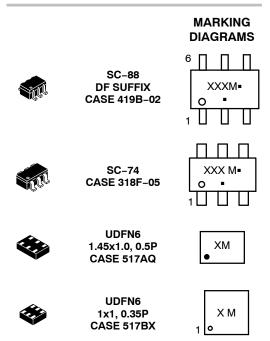


Figure 1. Logic Symbol



# ON Semiconductor®

#### www.onsemi.com



X, XXX = Specific Device Code
M = Date Code\*
= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

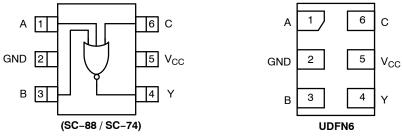


Figure 2. Pinout (Top View)

## **PIN ASSIGNMENT**

Pin	Function
1	Α
2	GND
3	В
4	Y
5	V <sub>CC</sub>
6	С

## **FUNCTION TABLE** $(Y = \overline{A + B + C})$

	Output		
Α	В	С	Υ
Н	Х	Х	L
Х	Н	Х	L
Х	Х	Н	L
L	L	L	Н

X = Don't Care

#### **MAXIMUM RATINGS**

Symbol	Characteristics	Value	Units	
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +6.5	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +6.5	V
V <sub>OUT</sub>	DC Output Voltage	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V <sub>CC</sub> = 0 V)	-0.5 to V <sub>CC</sub> +0.5 -0.5 to +6.5 -0.5 to +6.5	V
I <sub>IK</sub>	DC Input Diode Current, V <sub>IN</sub> < GND		-50	mA
lok	DC Output Diode Current, V <sub>OUT</sub> < GND		-50	mA
l <sub>out</sub>	DC Output Source/Sink Current		±50	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
$T_L$	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	°C/W
P <sub>D</sub>	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity		Level 1	-
F <sub>R</sub>	Flamebility Rating	Oxygen Index: 28 to 34	UL 94-V-0 @ 0.125 in	-
V <sub>ESD</sub>	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I <sub>LATCHUP</sub>	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri–stated.

- 2. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
- 3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
- 4. Tested to EIA/JESD78 Class II.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Para	meter	Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		1.65	5.5	V
V <sub>IN</sub>	DC Input Voltage		0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	Active–Mode (High or Low State) Tri–State Mode (Note 1) $Power$ –Down Mode ( $V_{CC}$ = 0 V)	0 0 0	V <sub>CC</sub> 5.5 5.5	V
T <sub>A</sub>	Operating Temperature Range		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Transition Rise or Fall Rate	$\begin{array}{c} V_{CC} = 1.65 \ V \ to \ 1.95 \ V \\ V_{CC} = 2.3 \ V \ to \ 2.7 \ V \\ V_{CC} = 3.0 \ V \ to \ 3.6 \ V \\ V_{CC} = 4.5 \ V \ to \ 5.5 \ V \end{array}$	0	20 20 10 5	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

			V <sub>cc</sub>		T <sub>A</sub> = 25°C		T <sub>A</sub> = -55°C	to +125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
V <sub>IH</sub>	High-Level		1.65 to 1.95	0.65 V <sub>CC</sub>	-	-	0.65 V <sub>CC</sub>	-	V
	Input Voltage		2.3 to 5.5	0.70 V <sub>CC</sub>	-	_	0.70 V <sub>CC</sub>	_	
$V_{IL}$	Low-Level		1.65 to 1.95	_	-	0.35 V <sub>CC</sub>	-	0.35 V <sub>CC</sub>	٧
	Input Voltage		2.3 to 5.5	_	-	0.30 V <sub>CC</sub>	-	0.30 V <sub>CC</sub>	
V <sub>ОН</sub>	High-Level Output Voltage	$\begin{split} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -100  \mu\text{A} \\ I_{OH} &= -4 \text{ mA} \\ I_{OH} &= -8 \text{ mA} \\ I_{OH} &= -12 \text{ mA} \\ I_{OH} &= -16 \text{ mA} \\ I_{OH} &= -24 \text{ mA} \\ I_{OH} &= -32 \text{ mA} \end{split}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V <sub>CC</sub> - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V <sub>CC</sub> 1.4 2.1 2.4 2.7 2.5 4.0	- - - - -	V <sub>CC</sub> - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	- - - - -	V
V <sub>OL</sub>	Low-Level Output Voltage	$\begin{array}{l} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OL} = 100  \mu\text{A} \\ I_{OL} = 4 \text{ mA} \\ I_{OL} = 8 \text{ mA} \\ I_{OL} = 12 \text{ mA} \\ I_{OL} = 16 \text{ mA} \\ I_{OL} = 24 \text{ mA} \\ I_{OL} = 32 \text{ mA} \end{array}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	1 1 1 1 1	- 0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55	- - - - -	0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
I <sub>IN</sub>	Input Leakage Cur- rent	V <sub>IN</sub> = 5.5 V or GND	1.65 to 5.5	-	-	±0.1	-	±1.0	μΑ
l <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V	0	-	-	1.0	-	10	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5	_	-	1.0	-	10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

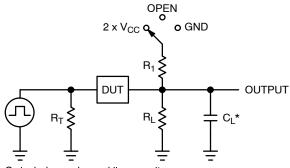
## **AC ELECTRICAL CHARACTERISTICS**

				T <sub>A</sub> = 25°C		$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$			
Symbol	Parameter	Test Condition	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Units
t <sub>PLH</sub> ,		$R_L = 1 \text{ M}\Omega$ , $C_L = 15 \text{ pF}$	1.65 to 1.95	-	10.0	18.5	-	19.0	ns
t <sub>PHL</sub>	(A or B or C) to Y (Figures 3 and 4)	$R_L = 1 \text{ M}\Omega$ , $C_L = 15 \text{ pF}$	2.3 to 2.7	ı	5.0	10.5	_	11.0	
	,	$R_L = 1 \text{ M}\Omega$ , $C_L = 15 \text{ pF}$	3.0 to 3.6	-	3.2	8.0	-	8.5	
		$R_L = 500 \Omega, C_L = 50 pF$		-	3.9	8.0	-	8.5	
		$R_L$ = 1 M $\Omega$ , $C_L$ = 15 pF	4.5 to 5.5	-	2.6	5.5	-	6.0	
		$R_L = 500 \Omega$ , $C_L = 50 pF$		-	2.9	5.5	_	6.0	

## **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Parameter Condition		Unit
C <sub>IN</sub>	Input Capacitance	$V_{CC}$ = 5.5 V, $V_I$ = 0 V or $V_{CC}$	4.0	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 5)	10 MHz, $V_{CC}$ = 3.3 V, $V_{IN}$ = 0 V or $V_{CC}$ 10 MHz, $V_{CC}$ = 5.0 V, $V_{IN}$ = 0 V or $V_{CC}$	23.0 30.0	pF

<sup>5.</sup>  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in}$ )  $I_{CC}$ .  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in}$ )  $I_{CC} \cdot V_{CC}$ .



Test	Switch Position	C <sub>L</sub> , pF	$R_L, \Omega$	$R_1, \Omega$	
t <sub>PLH</sub> / t <sub>PHL</sub>	Open	See AC Characteristics Table			
t <sub>PLZ</sub> / t <sub>PZL</sub>	2 x V <sub>CC</sub>	50	500	500	
t <sub>PHZ</sub> / t <sub>PZH</sub>	GND	50	500	500	

X = Don't Care

 $C_L$  includes probe and jig capacitance  $R_T$  is  $Z_{OUT}$  of pulse generator (typically 50  $\Omega)$  f = 1 MHz

Figure 3. Test Circuit

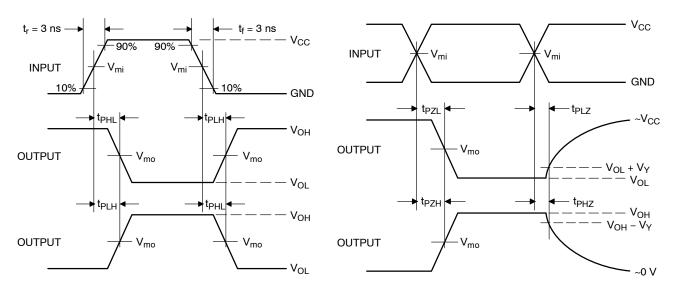


Figure 4. Switching Waveforms

		V <sub>m</sub>		
V <sub>CC</sub> , V	V <sub>mi</sub> , V	t <sub>PLH</sub> , t <sub>PHL</sub>	$t_{PZL}$ , $t_{PLZ}$ , $t_{PZH}$ , $t_{PHZ}$	V <sub>Y</sub> , V
1.65 to 1.95	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> / 2	0.15
2.3 to 2.7	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> / 2	0.15
3.0 to 3.6	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> / 2	0.3
4.5 to 5.5	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> / 2	0.3

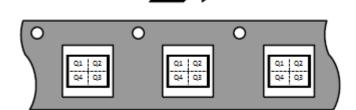
## **ORDERING INFORMATION**

Device	Package	Specific Device Code	Pin1 Orientation (See bellow)	Shipping <sup>†</sup>
NL17SZ27DFT2G (Contact ON Semiconductor)	SC-88	TBD	Q4	3000 / Tape & Reel
NL17SZ27DBVT1G	SC-74	AW	Q4	3000 / Tape & Reel
NL17SZ27MU1TCG (Contact ON Semiconductor)	UDFN6, 1.45 x 1.0, 0.5P	TBD	Q4	3000 / Tape & Reel
NL17SZ27MU3TCG (Contact ON Semiconductor)	UDFN6, 1.0 x 1.0, 0.35P	TBD	Q4	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

# Pin 1 Orientation in Tape and Reel

# **Direction of Feed**

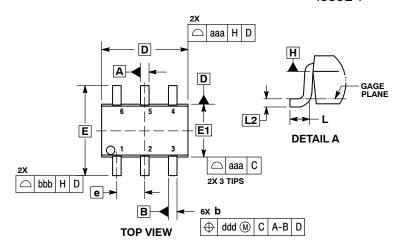


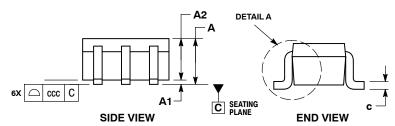
Capable.

#### PACKAGE DIMENSIONS

## SC-88/SC70-6/SOT-363

CASE 419B-02 **ISSUE Y** 





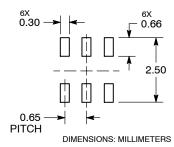
- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
  4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
  5. DATUMS A AND B ARE DETERMINED AT DATUM H.
  6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
  7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION

- DIMENSION 5 DOES NOT INCLUDE DAMBAR PROTRUSION.
  ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN
  EXCESS OF DIMENSION 5 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER

	MIL	LIMETE	RS	INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65 BS	С	0	.026 BS	С
L	0.26	0.36	0.46	0.010	0.014	0.018
L2		0.15 BS	C		0.006 BS	SC
aaa		0.15			0.006	
bbb	0.30				0.012	-
ccc	0.10				0.004	
ddd		0.10			0.004	

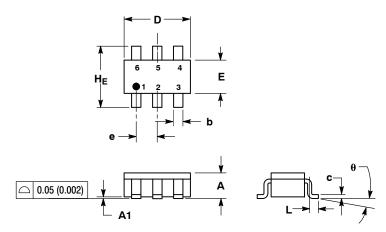
#### **RECOMMENDED SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **PACKAGE DIMENSIONS**

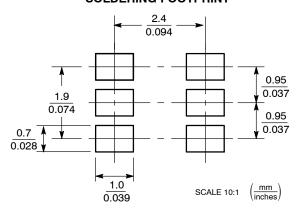
SC-74 CASE 318F-05 **ISSUE N** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
  THICKNESS OF BASE MATERIAL.
  4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
С	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	_	10°	0°	_	10°

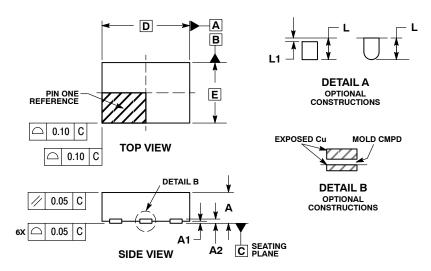
# **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

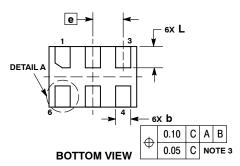
#### **PACKAGE DIMENSIONS**

UDFN6, 1.45x1.0, 0.5P CASE 517AQ ISSUE O

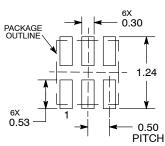


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
A2	0.07 REF		
b	0.20	0.30	
D	1.45 BSC		
Е	1.00 BSC		
e	0.50 BSC		
L	0.30	0.40	
L1		0.15	



# **MOUNTING FOOTPRINT**

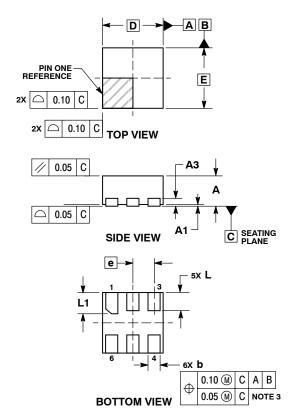


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

UDFN6, 1x1, 0.35P CASE 517BX **ISSUE O** 

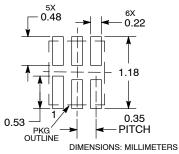


#### NOTES

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  DIMENSION 6 APPLIES TO PLATED
  TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. PACKAGE DIMENSIONS EXCLUSIVE OF
- BURRS AND MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.12	0.22
D	1.00 BSC	
E	1.00 BSC	
е	0.35 BSC	
L	0.25	0.35
L1	0.30	0.40

#### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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